



P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 20	0.061 at $V_{GS} = - 4.5$ V	- 4.4	7.6 nC
	0.080 at $V_{GS} = - 2.5$ V	- 3.8	
	0.110 at $V_{GS} = - 1.8$ V	- 3.3	
	0.165 at $V_{GS} = - 1.5$ V	- 0.5	

FEATURES

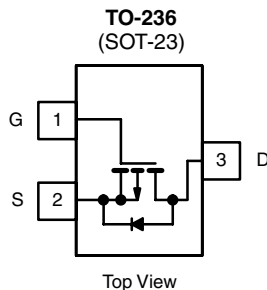
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Typical ESD Performance 2000 V
- Built in ESD Protection with Zener Diode
- Compliant to RoHS Directive 2002/95/EC



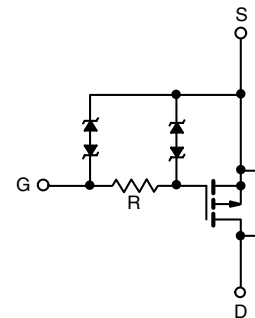
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices



Si2377EDS (P6)*
* Marking Code



P-Channel MOSFET

Ordering Information: Si2377EDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$ - 4.4	A
		$T_C = 70^\circ\text{C}$ - 3.5	
		$T_A = 25^\circ\text{C}$ - 3.7 ^{b, c}	
		$T_A = 70^\circ\text{C}$ - 2.9 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 20	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$ - 1.5	
		$T_A = 25^\circ\text{C}$ - 1.0 ^{b, c}	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$ 1.8	W
		$T_C = 70^\circ\text{C}$ 1.1	
		$T_A = 25^\circ\text{C}$ 1.25 ^{b, c}	
		$T_A = 70^\circ\text{C}$ 0.8 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	80	100	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	R_{thJF}	55	70	

Notes:

- $T_C = 25^\circ\text{C}$.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under Steady State conditions is 130 $^\circ\text{C/W}$.

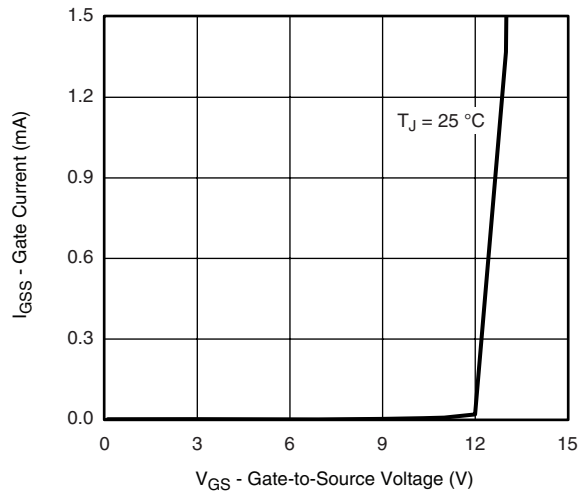
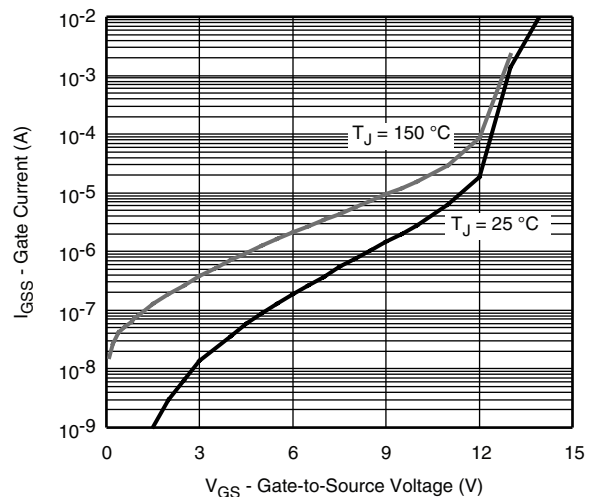
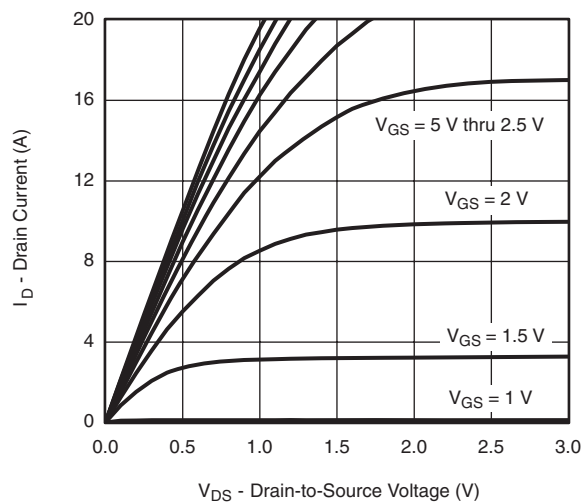
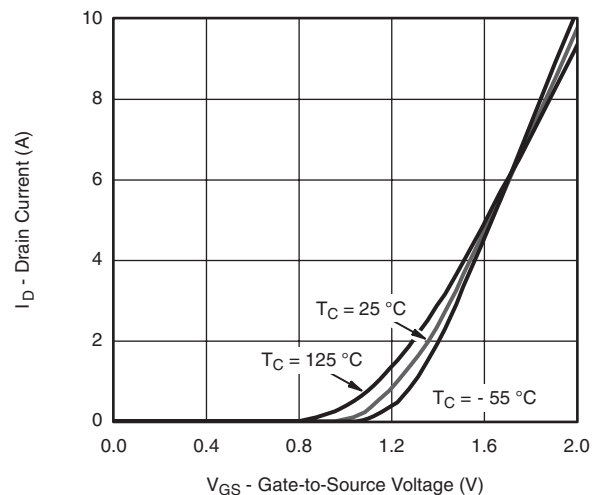
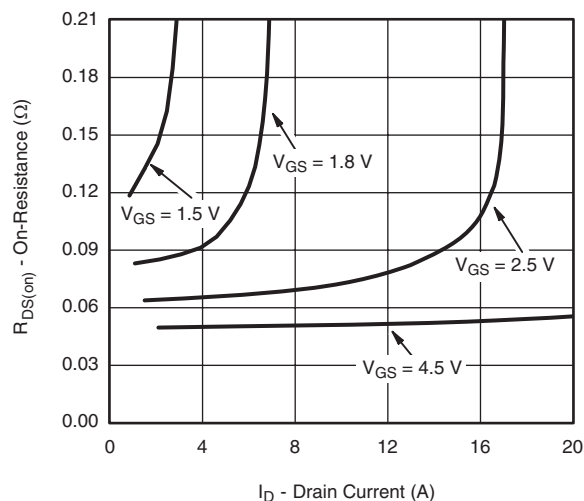
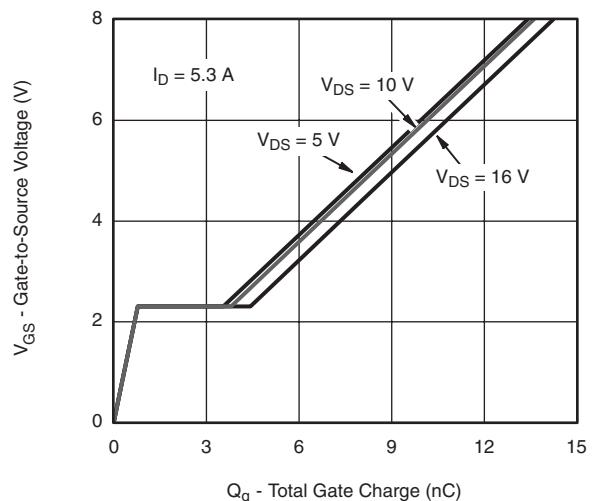
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 13		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.5			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 1	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 6	μA	
		V _{DS} = 0 V, V _{GS} = ± 4.5 V			± 0.5		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 15			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.2 A		0.050	0.061	Ω	
		V _{GS} = - 2.5 V, I _D = - 2.8 A		0.065	0.080		
		V _{GS} = - 1.8 V, I _D = - 1.5 A		0.090	0.110		
		V _{GS} = - 1.5 V, I _D = - 0.5 A		0.110	0.165		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 3.2 A		12		S	
Dynamic ^b							
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 5.3 A		14	21	nC	
Gate-Source Charge		V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 5.3 A		7.6	12		
			Q _{gs}		0.8		
Gate-Drain Charge	Q _{gd}			3.1			
Gate Resistance	R _g	f = 1 MHz	0.4	2	4	kΩ	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2.3 Ω I _D ≅ - 4.3 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		0.20	0.3	μs	
Rise Time	t _r			1.00	1.50		
Turn-Off Delay Time	t _{d(off)}			4.00	6.00		
Fall Time	t _f			2.00	3.00		
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2.3 Ω I _D ≅ - 4.3 A, V _{GEN} = - 8 V, R _g = 1 Ω		0.09	0.14		
Rise Time	t _r			0.40	0.60		
Turn-Off Delay Time	t _{d(off)}			5.20	7.80		
Fall Time	t _f			2.30	3.50		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 1.5	A	
Pulse Diode Forward Current	I _{SM}				- 20		
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 3 A, dI/dt = 100 A/μs, T _J = 25 °C		30	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			20	40	nC	
Reverse Recovery Fall Time	t _a			13		ns	
Reverse Recovery Rise Time	t _b			17			

Notes:

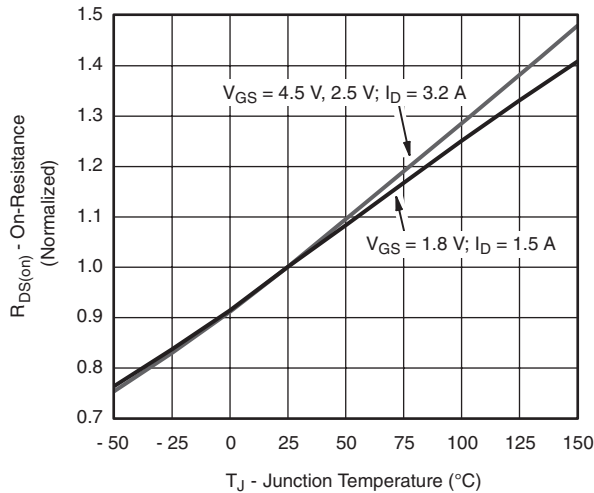
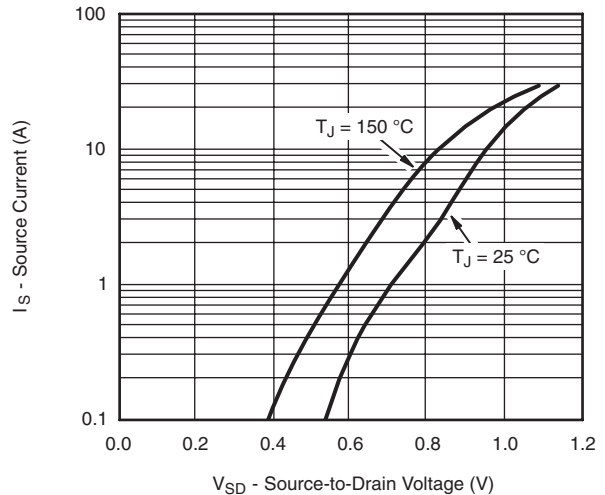
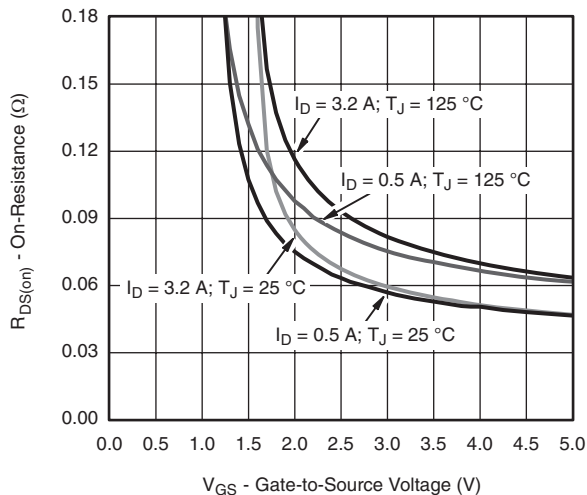
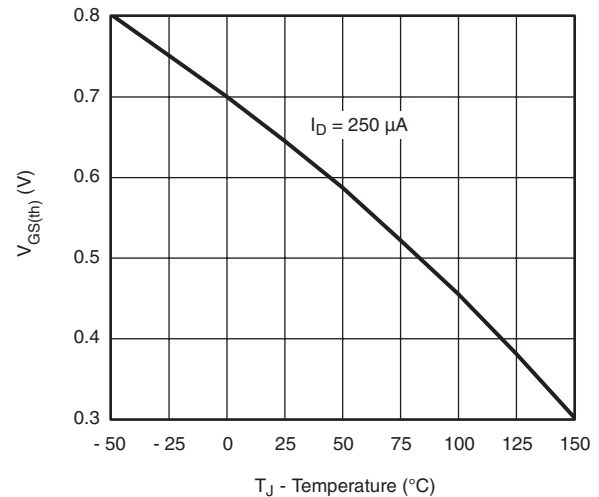
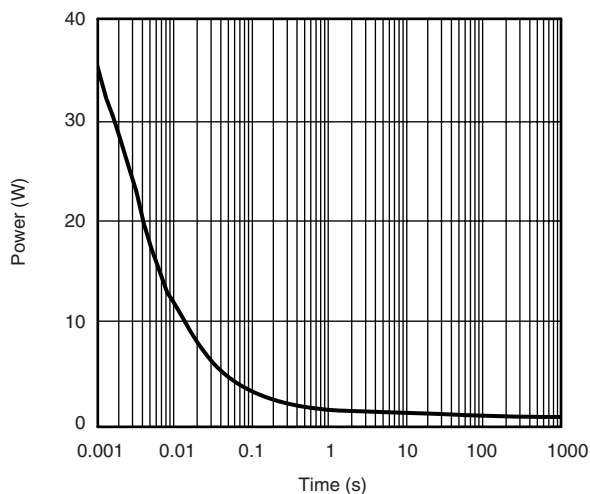
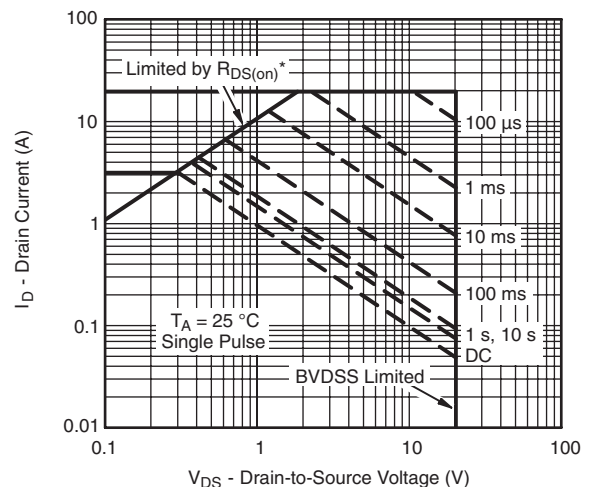
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

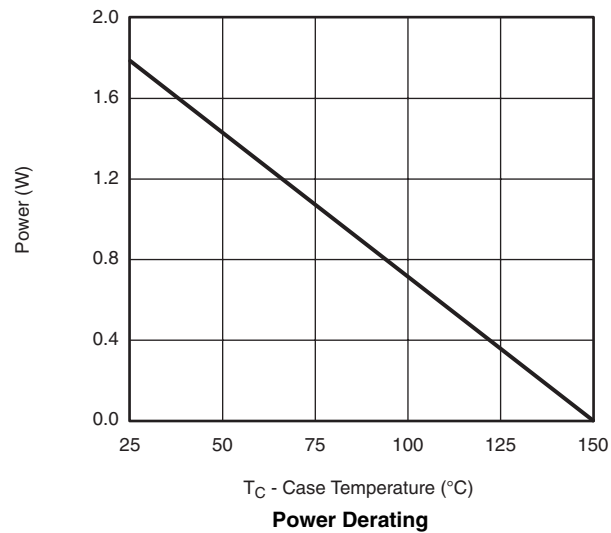
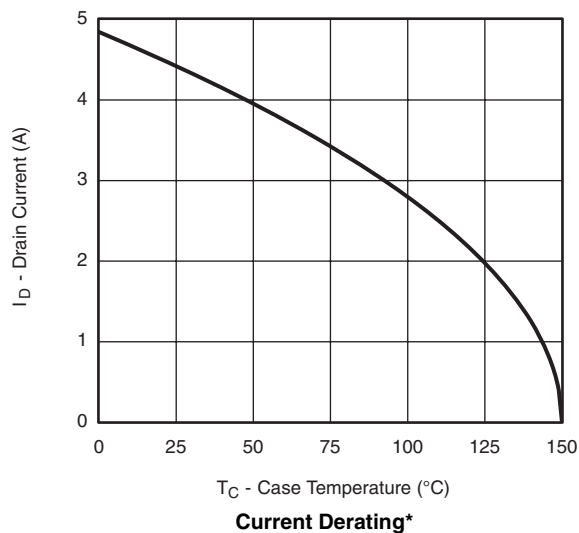
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Gate Current vs. Gate-Source Voltage

Gate Current vs. Gate-Source Voltage

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Gate Charge

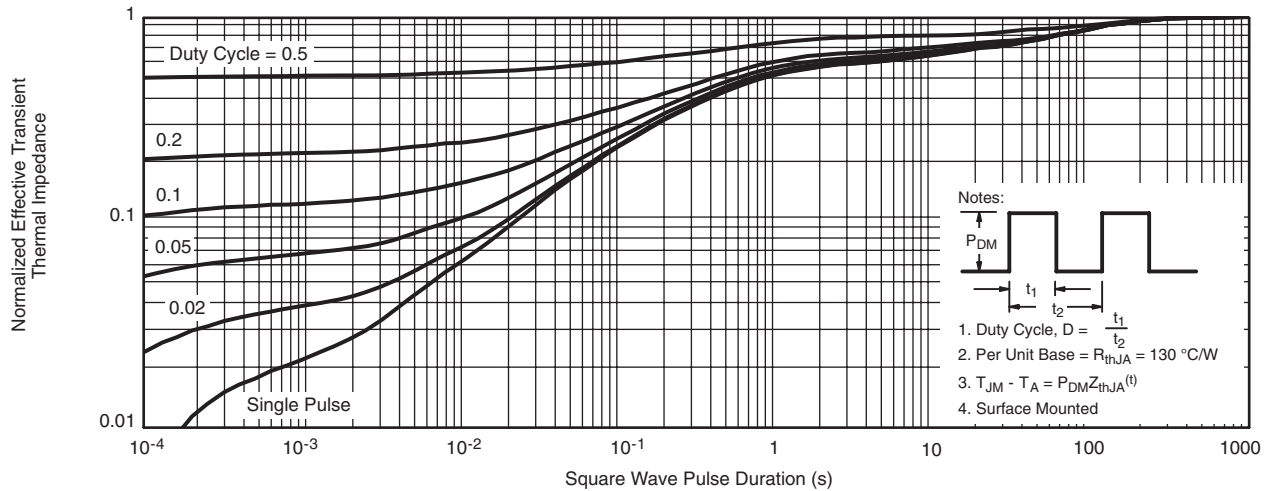
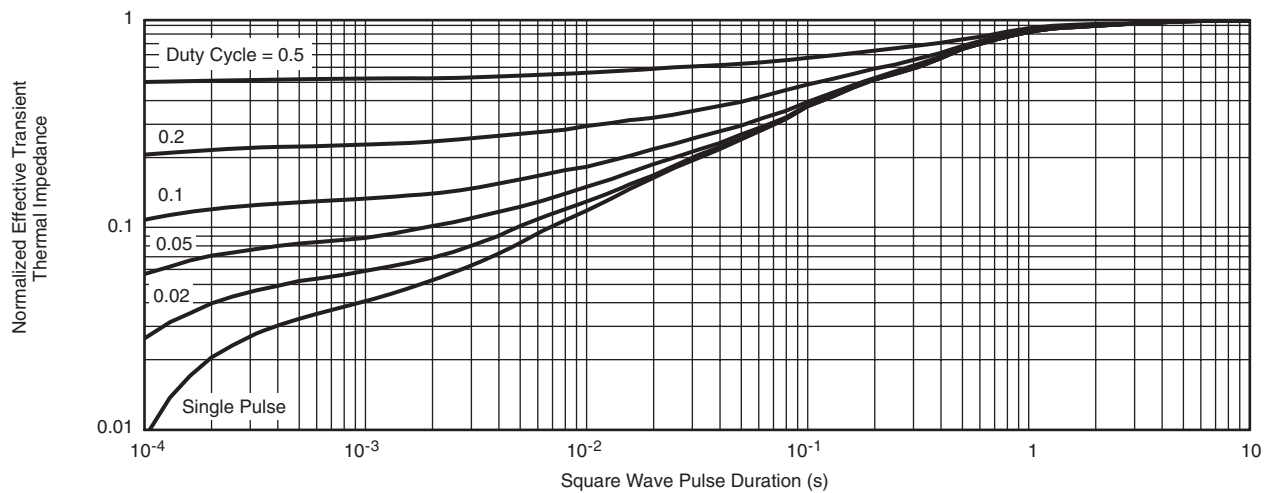
Si2377EDS

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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